



PTSMC-01-1020B

September 24, 2003

TO: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/613,606 07/03/03

Ying-Lin Chen et al.

A NEW APPROACH TO PREVENT SPACER
UNDERCUT BY LOW TEMPERATURE
NITRIDATION

Grp. Art Unit: -----

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on September 26, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 9/26/03

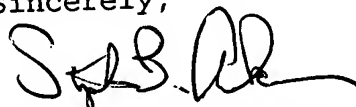
U.S. Patent 6,200,868 to Mase et al., "Insulated Gate Type Semiconductor Device and Process for Producing the Device," discusses a nitridation process to prevent gate spacer undercut.

U.S. Patent 6,187,676 to Kim et al., "Integrated Circuit Insulated Electrode Forming Methods Using Metal Silicon Nitride Layers, and Insulated Electrodes so Formed," discusses a nitridation process to cover an undercut.

U.S. Patent 6,144,071 to Gardner et al., "Ultrathin Silicon Nitride Containing Sidewall Spacers for Improved Transistor Performance," discloses a transistor provided having a pair of sidewall spacers, each preferably including an ultrathin silicon nitride layer, adjacent to opposed sidewall surfaces of a gate conductor on a semiconductor substrate.

U.S. Patent 5,939,333 to Hurley et al., "Silicon Nitride Deposition Method," the method in accordance with the present invention is an improved method of forming silicon nitride films to improve the characteristics of semiconductor devices fabricated using silicon nitride films.

Sincerely,

A handwritten signature in black ink, appearing to read "S. B. Ackerman", with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

Application Number

TSMC-01-1020B

10/613,606

Applicant

Ying-Lin Chen et al.

Filing Date

07/03/03

Draw Art Unit

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
6200868	3/13/01	Mase et al.	438	301	7/31/98
6187676	2/13/01	Kim et al.	438	656	8/14/98
6144071	11/7/00	Gardner et al.	257	344	9/3/98
5939333	8/17/99	Hurley et al.	437	241	5/30/96

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.